EXPRESS MAIL LABEL NO. EV314045464US

DATED: 03 FEBRUARY 2003 ATTORNEY DOCKET: MXIC 1564-1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of Inventor:	Group Art Unit: unknown		
Hsiang Lan Lung	Examiner: unknown		
Application No			
Filed: 03 February 2004 (herewith)	CUSTOMER NO. 22470		

Title: Trap Read Only Non-Volatile Memory (TROM)

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.56

Sir:

It is requested that the information identified in this statement be considered by the Examiner and made of record in the above-identified application. This statement is not intended to represent that a search has been made or that the information cited in the statement is, or is considered to be, material to patentability as defined in 37 C.F.R. 1.56.

Enclosed with this statement is a Form PTO-SB/08. The Examiner is requested to initial the form and return it to the undersigned in accordance with M.P.E.P. 609.

Also enclosed with this statement is a copy of each cited document as required by 37 C.F.R. 1.98. The exception to this, in accordance with the 05 August 2003 Official Gazette Notice in which the USPTO waives the requirement for submitting copies of U.S. Patent and Publications for cases filed after 30 June 2003, is that copies of U.S. Patent documents and copies of U.S. Patent publications are not being submitted. Document C7 is also not enclosed because, although it is viewable on the listed website, it cannot be printed. The Examiner is requested to view the reference online.

This statement should be considered under 37 C.F.R. 1.97(b) because it is being filed within three months of the filing date of an application other than a continued prosecution application under 37 C.F.R. 1.53(d).

Fee Authorization. The Commissioner is hereby authorized to charge underpayment of any additional fees or credit any overpayment associated with this communication to Deposit Account No. 50-0869 (MXIC 1564-1). A copy of this authorization is enclosed.

Respectfully submitted,

HAYNES BEFFEL & WOLFELD LLP

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Date: 3 Feb-04

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Substitu	ite for form 1449A/PTC)		Complete if Known			
INFORMATION BIOOLOGUES				Application Number			
INFORMATION DISCLOSURE				Filing Date	3 February 2004 (herewith)		
STA	TEMENT B	MENT BY APPLICANT First I		First Named Inventor Hisang Lan Lung			
				Group Art Unit			
	(use as many shee	ets as	necessary)	Examiner Name			
Sheet	1	of	2	Attorney Docket Number	MXIC 1564-1		

	U.S. PATENT DOCUMENTS								
Examiner Initials	Cite No.1	U.S. Patent Docum Kind C Number (if kno	Code ²	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear			
	A1	4,959,812		Momodomi et al.	09-25-1990				
	A2	5,270,969		Iwahashi	12-14-1993				
	A3	5,424,569		Prall	06-13-1995				
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	A13	2002/0179958		Kim	12-05-2002				
	A14								
	A15								
	A16								
	A17								
	A18								
	A19								
	A20								

	FOREIGN PATENT DOCUMENTS									
	Cite	F	oreign Patent Do	cument	Name of Patentee or	Date of Publication of	Pages, Columns, Lines,	T		
	No.1	Office ³	Number4	Kind Code ⁵ (if known)	Applicant of Cited Document	Cited Document MM-DD-YYYY	Where Relevant Passages or Relevant Figures Appear	Т6		
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Examiner	Date	
Signature	Considered	

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.



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Substitu	ute for form 1449B/PTC)		Compl te if Known		
				Application Number		
INFORMATION DISCLOSURE Filing Date 3 February 2004 (herewith				3 February 2004 (herewith)		
STATEMENT BY APPLICANT		First Named Inventor	Hsiang Lan Lung			
				Group Art Unit		
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Sheet	2	of	2	Attorney Docket Number	MXIC 1564-1	

		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS								
Examiner Initials	Cite No.1									
	C1	DE BLAUWE, JAN, "Nanocrystal Nonvolatile Memory Devices," IEEE Transactions on Nanotechnology, Vol. 1, No. 1 (March 2002) 72-77								
	C2	LEE, JAE-DUK, "Effects of Floating-Gate Interference on NAND Flash Memory Cell Operation," IEEE Electron Device Letters, Vol. 23, No. 5 (May 2002), 264-266								
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Examiner	Date	
Signature	Considered	

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